

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

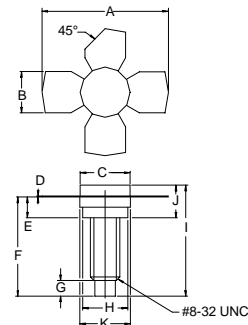
The **ASI 2N4429** is Designed for Class C Amplifier Applications Up to 1,000 MHz.

**FEATURES:**

- $P_G = 7.5$  dB Typ. at 1.0 W/1000 MHz
- Emitter Ballasting for Ruggedness
- **Omnigold™** Metallization System

**MAXIMUM RATINGS**

$I_C$	1.0 A
$V_{CB}$	45 V
$P_{DISS}$	7.0 W @ $T_C = 25^\circ\text{C}$
$T_J$	-65 to +200 $^\circ\text{C}$
$T_{STG}$	-65 to +150 $^\circ\text{C}$
$\theta_{JC}$	25 $^\circ\text{C/W}$

**PACKAGE STYLE .280 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

**ORDER CODE: ASI10900**
**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 1$ mA	45			V
$BV_{CER}$	$I_C = 20$ mA $R_{BE} = 10 \Omega$	45			V
$BV_{EBO}$	$I_E = 1$ mA	3.5			V
$I_{CBO}$	$V_{CE} = 28$ V			250	$\mu\text{A}$
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 100$ mA	15		150	---
$F_t$	$V_{CE} = 20$ V $I_C = 100$ mA	600			MHz
$C_{ob}$	$V_{CB} = 28$ V $f = 1.0$ MHz			5.0	pF
$P_G$	$V_{CE} = 28$ V $P_{OUT} = 5.0$ W $f = 1,000$ MHz	6.5	7.5		dB
$\eta_c$		40	50		%